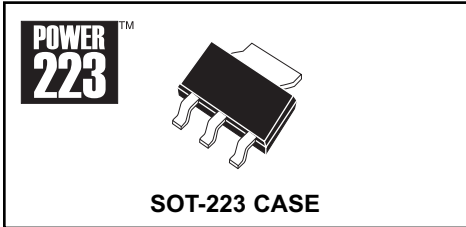


CZT3150
SURFACE MOUNT
NPN SILICON POWER TRANSISTOR



CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT3150 type is a NPN Silicon Power Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high current, high gain, fast switching applications.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C)

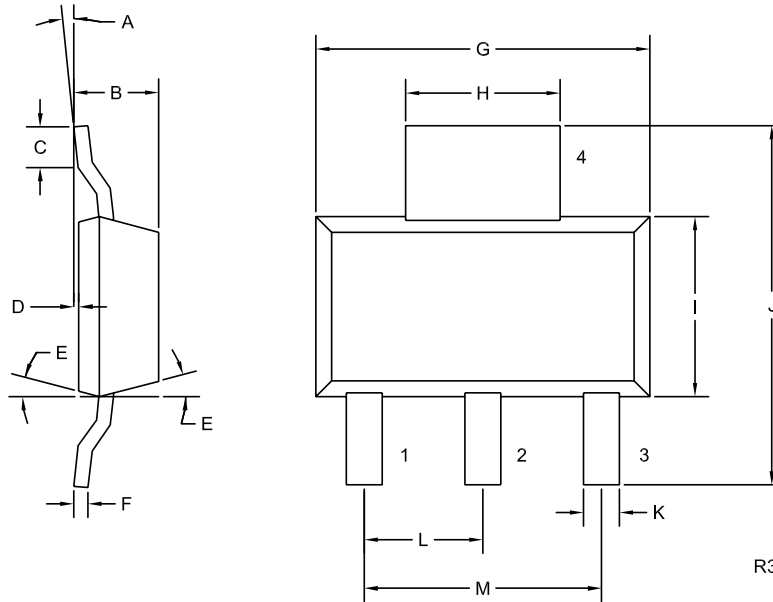
			UNITS
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	7.0	V
Collector Current	I _C	5.0	A
Base Current	I _B	1.0	A
Power Dissipation	P _D	2.0	W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	62.5	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} =50V			1.0	μA
I _{EBO}	V _{EB} =7.0V			1.0	μA
BV _{CEO}	I _C =10mA	25			V
V _{CE(SAT)}	I _C =3.0A, I _B =150mA			0.5	V
V _{CE(SAT)}	I _C =4.0A, I _B =200mA			0.6	V
V _{BE(SAT)}	I _C =3.0A, I _B =150mA			1.10	V
V _{BE(SAT)}	I _C =4.0A, I _B =200mA			1.40	V
h _{FE}	V _{CE} =2.0V, I _C =500mA	250		550	
h _{FE}	V _{CE} =2.0V, I _C =2.0A	150			
h _{FE}	V _{CE} =2.0V, I _C =5.0A	50			
f _T	V _{CE} =6.0V, I _C =50mA, f=200MHz		150		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz			50	pF

R5 (04-May 2005)

SOT-223 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

MARKING CODE:

FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	10°	0°	10°
B	0.059	0.071	1.50	1.80
C	0.018	---	0.45	---
D	0.000	0.004	0.00	0.10
E	15°		15°	
F	0.009	0.014	0.23	0.35
G	0.248	0.264	6.30	6.70
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.70
J	0.264	0.287	6.70	7.30
K	0.024	0.033	0.60	0.85
L	0.091		2.30	
M	0.181		4.60	

SOT-223 (REV: R3)